# **EXCITONS IN NANOSTRUCTURES**

Introduction

### **Reasons for nano**

It is desirable to control properties of devices

The decision is NANOSTRUCTURES

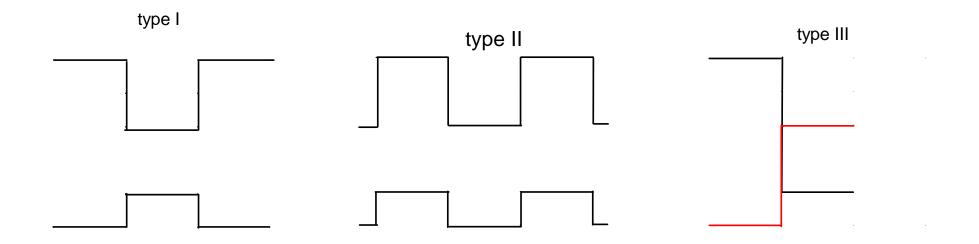
#### **Kinds of nanostructures**

- •Single heterojunctions
- •Quantum wells
- •Quantum wires
- •Quantum dots
- •Superlattices

#### **Types of nanostructures**

QWs can be of Type I Type II Type III

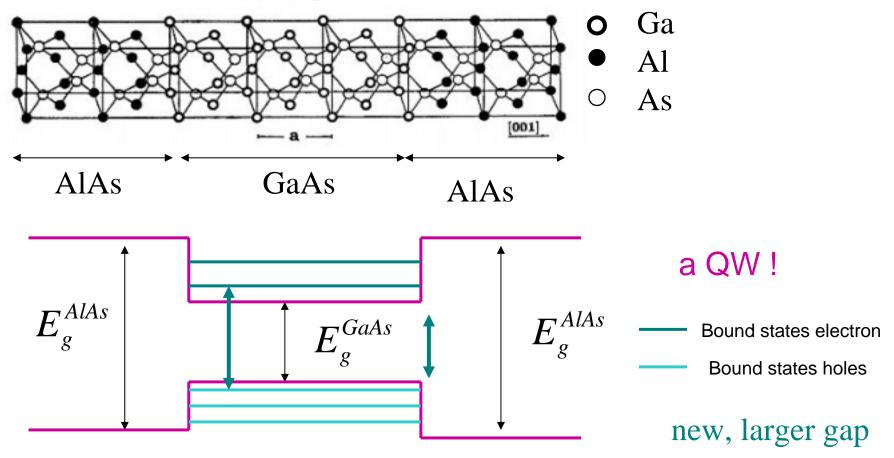
#### **Types of heterostructures**



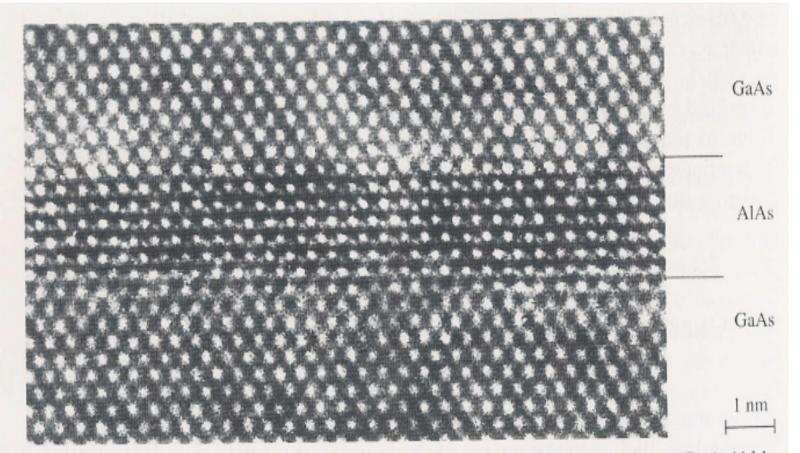
The main advantage of nanostructures arise from quantization

#### The principle of a semiconductor QW

New artificial material formed by thin layers of semiconductors with different energy gaps

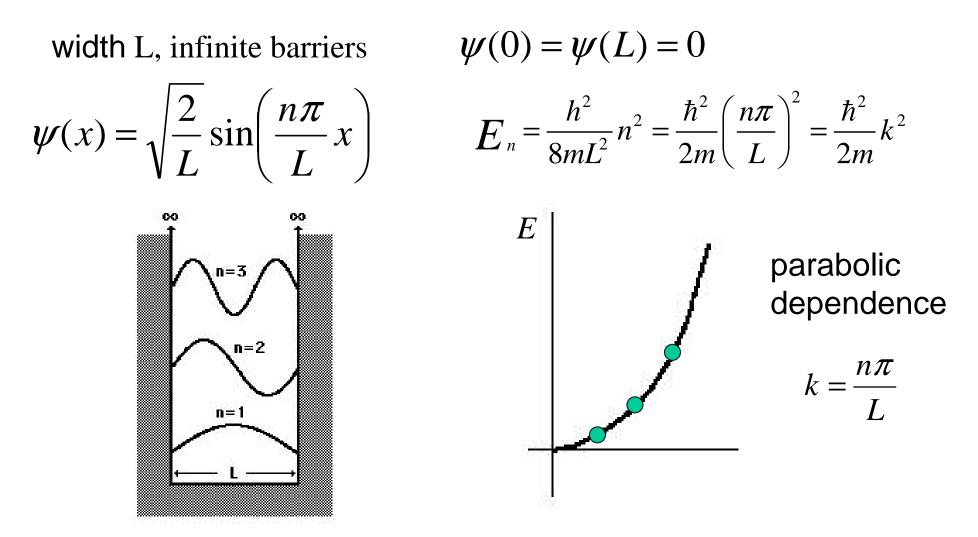


## semiconductor QW

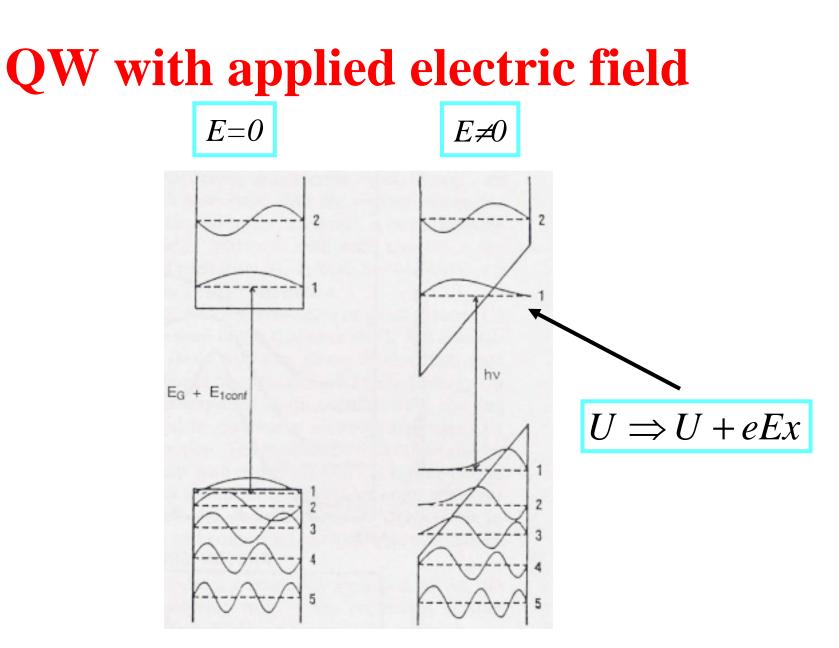


**Fig. 9.1.** High resolution transmission electron micrograph (TEM) showing a GaAs/AlAs superlattice for a [110] incident beam. (Courtesy of K. Ploog, Paul Drude Institute, Berlin.) In spite of the almost perfect interfaces, try to identify possible Al atoms in Ga sites and vice versa

### Quantum well (QW)



Quantization in two, three dimensions = NW, QD

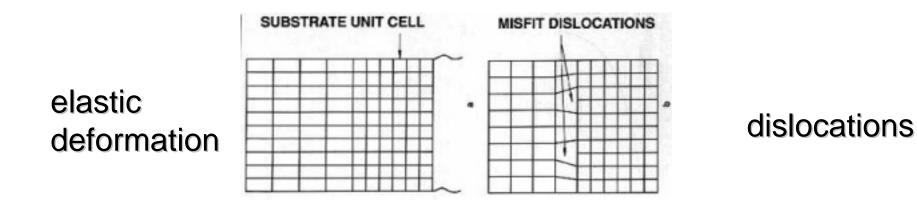


We can control the wavefunction not only due to quantization, but also by external fields

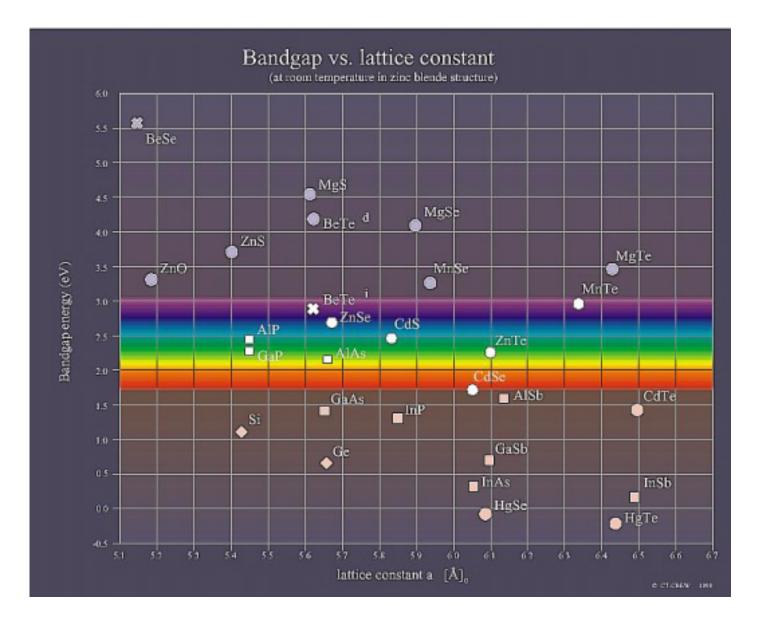
# growth of sharp interfaces

Each material has an optimal lattice parameter a

layer by layer growth proceeds nicely if the lattice parameters of the semiconductors used have almost the same lattice parameter (<1 % difference)



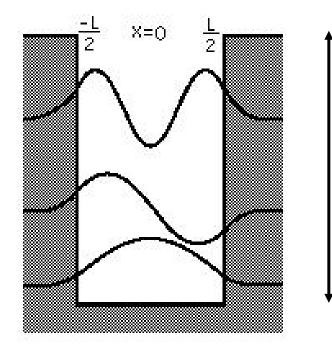
# Energy gaps and lattice parameters



## Tunneling

U

QW with barriers of finite height U



In the barrier

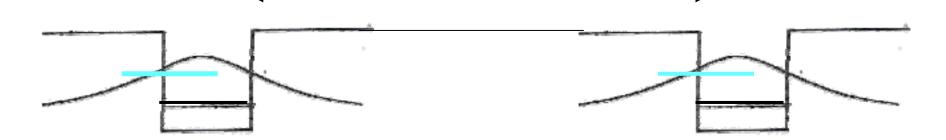
 $\psi \approx e^{-Cx} = e^{-x/l_d}$  $\sqrt{\frac{\hbar^2}{2m(U-E)}}$  $l_d = C^{-1}$ 

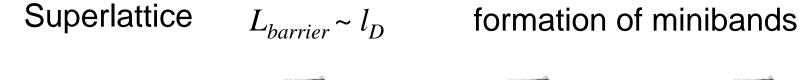
Wavefunction decays more slowly in the barrier when its energy gets closer to U

### **Multiple QW's versus superlattices (SL)**

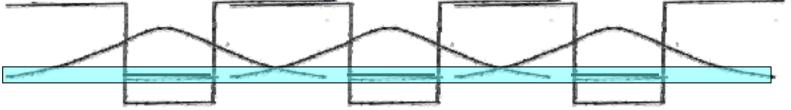
same energy level in each well

 $L_{barrier} >> l_D$  enhances absorption/emission





Multi QW



A new 3D material with tunable energy bands !